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APPLICATION N	Э.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/743,361	0/743,361 12/22/2003		Shin Hwa Li	98-P-009D1 (850063.529D1)	7964	
30423	7590	04/23/2004		EXAMINER		
STMICR	OELECTI	RONICS, INC.	GHYKA, ALEXANDER G			
MAIL ST	ATION 234	16				
1310 ELECTRONICS DRIVE				ART UNIT	ART UNIT PAPER NUMBER	
CARROLLTON, TX 75006				2812		

DATE MAILED: 04/23/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)	(0				
	10/743,361	LI ET AL.					
Office Action Summary	Examiner	Art Unit					
	Alexander G. Ghyka	2812					
The MAILING DATE of this communicate Period for Reply	ion appears on the cover sheet with	the correspondence add	lress				
A SHORTENED STATUTORY PERIOD FOR THE MAILING DATE OF THIS COMMUNICA:  Extensions of time may be available under the provisions of 37 after SIX (6) MONTHS from the mailing date of this communical. If the period for reply specified above is less than thirty (30) dated if NO period for reply is specified above, the maximum statutor. Failure to reply within the set or extended period for reply will, Any reply received by the Office later than three months after the earned patent term adjustment. See 37 CFR 1.704(b).	TION. CFR 1.136(a). In no event, however, may a repation. ya a reply within the statutory minimum of thirty ( y period will apply and will expire SIX (6) MONTT by statute, cause the application to become ABA	ly be timely filed 30) days will be considered timely. 4S from the mailing date of this cor NDONED (35 U.S.C. § 133).	nmunication.				
Status							
1) Responsive to communication(s) filed o	n						
2a) This action is <b>FINAL</b> . 2b)	☑ This action is non-final.						
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Disposition of Claims							
4) Claim(s) 1-9 is/are pending in the application 4a) Of the above claim(s) is/are versions.  5) Claim(s) is/are allowed.  6) Claim(s) 1-9 is/are rejected.  7) Claim(s) is/are objected to.  8) Claim(s) are subject to restriction.	vithdrawn from consideration.	ALEXANDE PRIMARY E AU 2 <sup>6</sup> Och	XAMINER				
Application Papers		<b>O</b>					
9) The specification is objected to by the Einstein The drawing(s) filed on is/are: a)  Applicant may not request that any objection Replacement drawing sheet(s) including the should on the should be	☐ accepted or b)☐ objected to by n to the drawing(s) be held in abeyance correction is required if the drawing(s	e. See 37 CFR 1.85(a). ) is objected to. See 37 CF					
Priority under 35 U.S.C. § 119							
12) Acknowledgment is made of a claim for  a) All b) Some * c) None of:  1. Certified copies of the priority doc  2. Certified copies of the priority doc  3. Copies of the certified copies of the application from the International  * See the attached detailed Office action for	cuments have been received. cuments have been received in Ap he priority documents have been re Bureau (PCT Rule 17.2(a)).	plication No eceived in this National S	Stage				
Attachment(s)  1) Notice of References Cited (PTO-892)  2) Notice of Draftsperson's Patent Drawing Review (PTO-3) Information Disclosure Statement(s) (PTO-1449 or PTO Paper No(s)/Mail Date	948) Paper No(s)/	mmary (PTO-413) Mail Date ormal Patent Application (PTO	-152)				

### **DETAILED ACTION**

## Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1, 2 and 6 are rejected under 35 U.S.C. 102(b) as being anticipated by Ngo et al (US 6,127,261).

Ngo et al teach a method of forming interlayer dielectric layers including a substrate (102); a patterned oxide layer (104) disposed over the substrate (102); a layer of undoped silicate glass (112) disposed over the patterned oxide layer (104); a layer of borophosphorous silicate glass (106) over the layer of undoped silicate glass (112); and a planarized layer of plasma enhanced tetraethyl orthosilicate (110) over at least a portion of the borophosphorus silicate glass layer (106), the layers of the undoped silicate glass layer (112), the borophosphorus silicate glass layer (106) and the planarized plasma enhanced tetraethyl orthosilicate layer (110) together forming a premetal dielectric layer (column 1, line 29-column 5, line 15), as required by Claim 1. See column 1, line 29 to column 5, line 15. Moreover, Ngo et al disclose a CMP process as required in Claim 2. See column 3, lines 40-50. Furthermore, Ngo et al teach that the trilayer dielectric is 13700 Angstroms which anticipates Claim 6 which requires less than 15000 Angstroms. See column 3, lines 1-5. Therefore, Claims 1-2 and 6 are anticipated.

## Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

Claims 4-5 rejected under 35 U.S.C. 103(a) as being unpatentable over Ngo et al (US 6,127,261).

Ngo et al is relied upon as discussed above. Ngo et al disclose that the TEOS layer has a thickness of 10200 Angstroms and the trilayer dielectric has a thickness of approximately 13700 Angstroms. See column 3, lines 1-10.

However, Ngo et al fail to teach the thicknesses of the USG and BPSG layers.

It would have been obvious for one of ordinary skill in the art to arrive at the presently claimed invention as the selection of the thicknesses in light of the parameters Art Unit: 2812

disclosed by Ngo et al is simply a matter of determining an optimum process condition by routine experimentation. See *In re Jones*, 162 USPQ 224 (CCPA 1955). Moreover, the discovery of an optimum value of a result effective variable in a known process is obvious. See *In re Boesch*, 205 USPQ 215 (CCPA 1980). Furthermore, as the cited prior art discloses overlapping ranges, a *prima facie* case of obviousness is established. See *In re Wertheim*.

Claims 3 and 7-9 are rejected under 35 U.S.C. 103(a) as being unpatentable over Ngo et al as applied to claims 1-2 and 4-6 above, and further in view of Dawson (US 5,503,882).

Ngo et al is relied upon as discussed above.

However, Ngo et al fail to teach forming a second layer of plasma enhanced tetraethyl orthosilicate overlying the planarized layer of plasma enhanced tetraethyl orthosilicate layer, directly overlying and being in contact with at least a portion of the borophosphorous silicate glass region having a planar surface.

Dawson (Figure 7 B) in a related method for planarizing integrated circuit topography teaches the steps of forming a planarized layer of plasma enhanced tetraethylorthosilicate (42); and a capping layer comprising a second layer of plasma enhanced tetraethyl orthosilicate (52) overlying the planarized layer of plasma enhanced tetraethyl orthosilicate layer (42). Dawson also discloses that the capping layer provides a barrier against water sorption into layers below the capping layer. See column 9, lines 4-20.

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It would have been obvious to one of ordinary skill in the art at the time of the invention was made to form the capping layer of Dawson onto the interlayer dielectric structure of Ngo et al and extend the capping in contact with the BPSG, for the benefit of providing a barrier against water sorption into the layers below the capping layer as disclosed by the Dawson reference. With respect to the thicknesses of the layers all this is simply a matter of determining an optimum process condition by routine experimentation. See *In re Jones*, 162 USPQ 224 (CCPA 1955). Moreover, the discovery of an optimum value of a result effective variable in a known process is obvious. See *In re Boesch*, 205 USPQ 215 (CCPA 1980). Furthermore, as the cited prior art discloses overlapping ranges, a *prima facie* case of obviousness is established. See *In re Wertheim*.

### Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Alexander G. Ghyka whose telephone number is (571) 272-1669. The examiner can normally be reached on Monday through Thursday during general business hours.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, John F Niebling can be reached on (571) 272-1679. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Application/Control Number: 10/743,361

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

AGG April 18, 2004

> ALEXANDER GHYKA PRIMARY EXAMINER

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